12 June 2014

Product data sheet

1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

3. Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- · Motors, lamps and solenoids

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	55	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>		-	-	11	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	36	W
Static characte	eristics		,				-
Boom	drain-source on-state	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C		-	97	125	mΩ
	resistance	V _{GS} = 5 V; I _D = 5 A; T _j = 175 °C; Fig. 11; Fig. 12		-	-	280	mΩ
		V_{GS} = 4.5 V; I_D = 5 A; T_j = 25 °C		-	-	155	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 11;$ Fig. 12		-	120	140	mΩ
Dynamic chara	acteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; V_{DS} = 44 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. } 13}$		-	2.6	-	nC



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 11 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	16	mJ

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D 1
2	D	Drain		
3	S	source		G—U: 4
mb	D	mounting base; connected to drain	1 3 DPAK (SOT428)	mbb076 S

6. Ordering information

Table 3. Ordering information

Table 6. Grading in	TOTTILICATION					
Type number	Package					
	Name	Description	Version			
BUK92150-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428			
BUK92150-55A/CD	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428			

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK92150-55A	9215055A
BUK92150-55A/CD	

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$	-	55	V

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Symbol	Parameter	Conditions	Min	Max	Unit
V_{DGR}	drain-gate voltage	R _{GS} 20 kΩ	-	55	V
V _{GS}	gate-source voltage		-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	36	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	11	Α
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 3</u>	-	7.8	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 2	-	44	Α
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C
Source-drain o	liode				
I _S	source current	T _{mb} = 25 °C	-	11	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	44	Α
Avalanche rug	gedness				,
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 11 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped	-	16	mJ

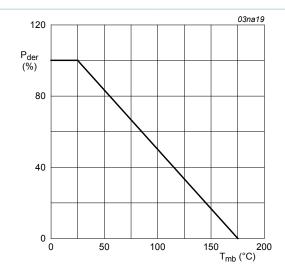


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

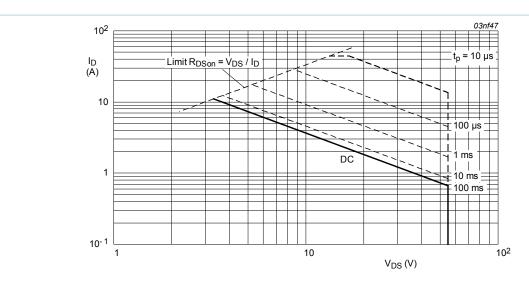


Fig. 2. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$$T_{mb} = 25$$
°C; I_{DM} is single pulse

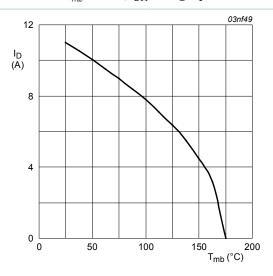


Fig. 3. Continuous drain current as a function of mounting base temperature

$$V_{\textit{GS}} \geq 4.5 V I_{\textit{der}} = \frac{I_{D}}{I_{D(25^{\circ}\textrm{C})}} \times 100\,\%$$

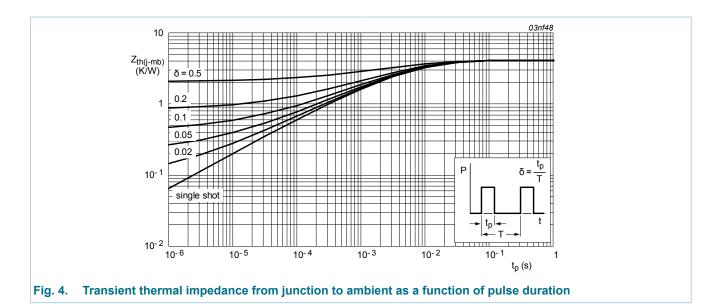
9. Thermal characteristics

Table 6. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4		-	-	4.1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient			-	71.4	-	K/W

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N-channel TrenchMOS logic level FET



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	M	n Ty	Max	Unit
Static chara	acteristics				1	
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	5	5 -	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 ^{\circ}\text{C}$	50) -	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	2.3	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 10	1	1.5	5 2	V
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	0	5 -	-	V	
I _{DSS} drain leakage current	drain leakage current	V _{DS} = 55 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ
	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.0)5 10	μΑ	
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C	-	97	125	mΩ
	resistance	V _{GS} = 5 V; I _D = 5 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	280	mΩ
		V _{GS} = 4.5 V; I _D = 5 A; T _j = 25 °C	-	-	155	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11;$ Fig. 12	-	12	0 140	mΩ

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	I _D = 5 A; V _{DS} = 44 V; V _{GS} = 5 V;	-	6	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13</u>	-	0.76	-	nC
Q_{GD}	gate-drain charge		-	2.6	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	240	338	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>	-	50	65	pF
C _{rss}	reverse transfer capacitance		-	40	58	pF
t _{d(on)}	turn-on delay time	V_{DS} = 20 V; R_{L} = 3.3 Ω ; V_{GS} = 5 V; $R_{G(ext)}$ = 10 Ω ; T_{j} = 25 °C	-	8	-	ns
t _r	rise time		-	57	-	ns
t _{d(off)}	turn-off delay time		-	16	-	ns
t _f	fall time		-	13	-	ns
L _D	internal drain inductance	measured from drain to centre of die; $T_j = 25 ^{\circ}\text{C}$	-	2.5	-	nH
L _S	internal source inductance	measured from source lead to source bond pad; T_j = 25 °C	-	7.5	-	nH
Source-dra	in diode		1		-	
V _{SD}	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 15$	-	0.85	1.2	V
t _{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = -100 A/ μ s; V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C	-	24	-	ns
Q _r	recovered charge		-	26	-	nC
						- 1

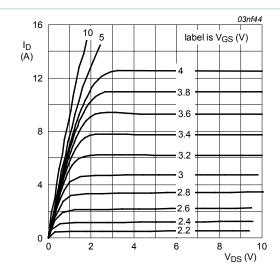


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

$$T_j = 25^{\circ}C$$

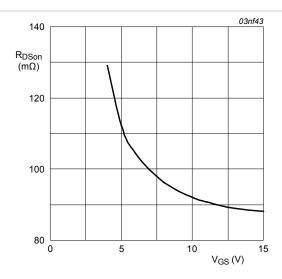


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 5A$$

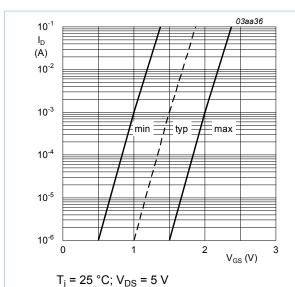


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

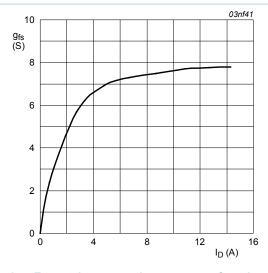


Fig. 8. Forward transconductance as a function of drain current; typical values

$$T_j = 25 \, {}^{\circ}C; \, V_{DS} = 25 \, V$$

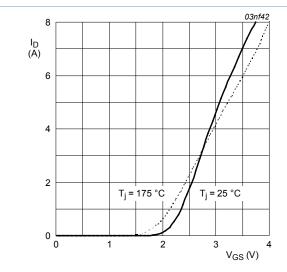


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values



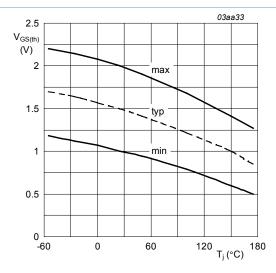


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 mA; V_{DS} = V_{GS}$$

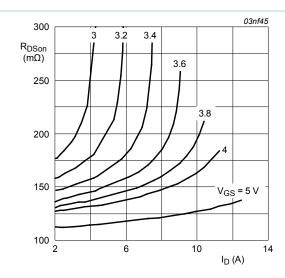


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^{\circ}C$$

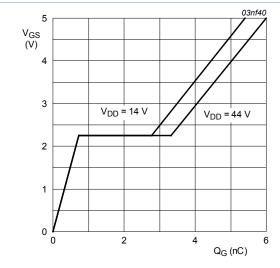


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 5A$$

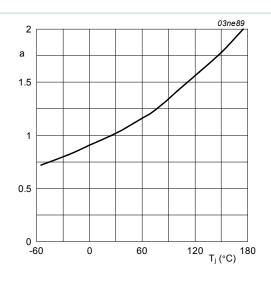


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

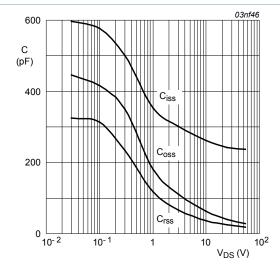


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

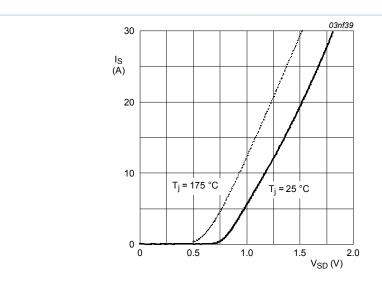
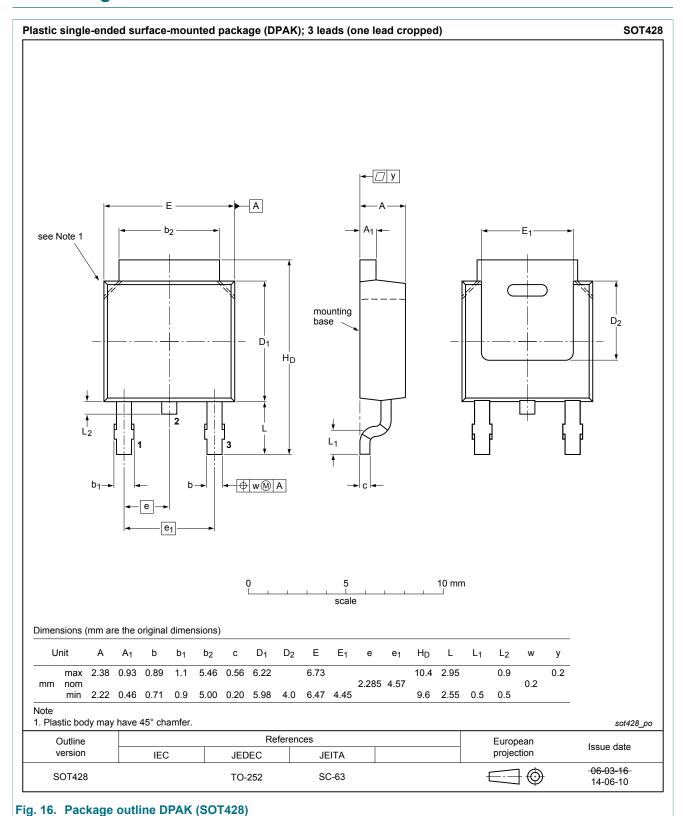


Fig. 15. Reverse diode current as a function of reverse diode voltage; typical values

$$V_{GS} = 0V$$

11. Package outline



12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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13. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	4
10	Characteristics	5
11	Package outline	10
12	Legal information	11
12.1	Data sheet status	11
12.2	Definitions	11
12.3	Disclaimers	11
12.4	Trademarks	12

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